

PRELIMINARY

CY7C1019**128K x 8 Static RAM****Features**

- **High speed**
— $t_{AA} = 10 \text{ ns}$
- **CMOS for optimum speed/power**
- **Center power/ground pinout**
- **Automatic power-down when deselected**
- **Easy memory expansion with \overline{CE} and \overline{OE} options**

Functional Description

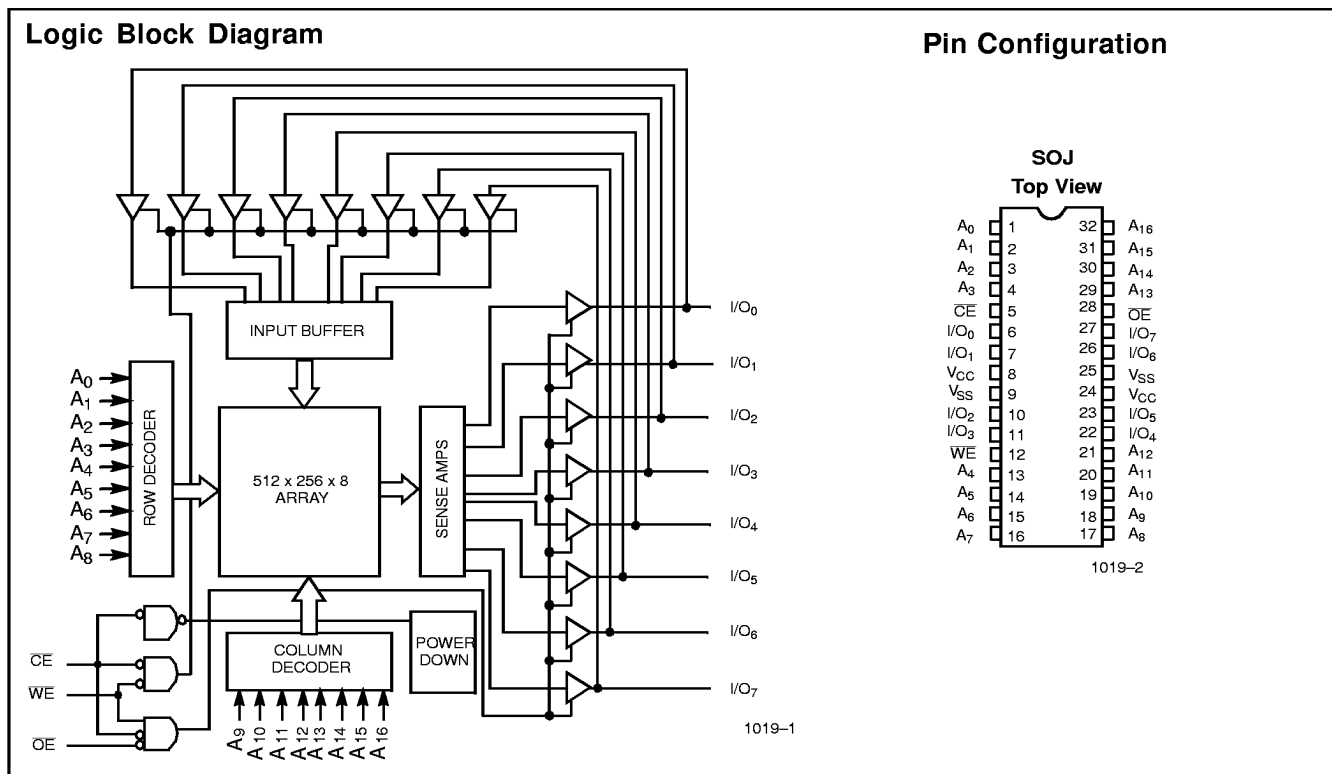
The CY7C1019 is a high-performance CMOS static RAM organized as 131,072 words by 8 bits. Easy memory expansion is provided by an active LOW chip enable (\overline{CE}), an active LOW output enable (\overline{OE}), and three-state drivers. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

Writing to the device is accomplished by taking chip enable (\overline{CE}) and write enable (\overline{WE}) inputs LOW. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking chip enable (\overline{CE}) and output enable (\overline{OE}) LOW while forcing write enable (\overline{WE}) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected (\overline{CE} HIGH), the outputs are disabled (\overline{OE} HIGH), or during a write operation (\overline{CE} LOW, and \overline{WE} LOW).

The CY7C1019 is available in standard 400-mil-wide SOJs.

**Selection Guide**

		7C1019-10	7C1019-12	7C1019-15
Maximum Access Time (ns)		10	12	15
Maximum Operating Current (mA)		240	220	200
	L	210	190	175
Maximum Standby Current (mA)		10	10	10
	L	1	1	1

Shaded areas contain advance information.

**Maximum Ratings**

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with
Power Applied -55°C to +125°C

Supply Voltage on V_{CC} to Relative GND^[1] -0.5V to +7.0V

DC Voltage Applied to Outputs
in High Z State^[1] -0.5V to $V_{CC} + 0.5V$

DC Input Voltage^[1] -0.5V to $V_{CC} + 0.5V$

Current into Outputs (LOW) 20 mA

Static Discharge Voltage >2001V
(per MIL-STD-883, Method 3015)

Latch-Up Current >200 mA

Operating Range

Range	Ambient Temperature ^[2]	V_{CC}
Commercial	0°C to +70°C	5V \pm 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	7C1019-10		7C1019-12		7C1019-15		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min.}, I_{OH} = -4.0 \text{ mA}$	2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min.}, I_{OL} = 8.0 \text{ mA}$		0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage		2.2	$V_{CC} + 0.3$	2.2	$V_{CC} + 0.3$	2.2	$V_{CC} + 0.3$	V
V_{IL}	Input LOW Voltage ^[1]		-0.3	0.8	-0.3	0.8	-0.3	0.8	V
I_{IX}	Input Load Current	$GND \leq V_I \leq V_{CC}$	-1	+1	-1	+1	-1	+1	μA
I_{OZ}	Output Leakage Current	$GND \leq V_I \leq V_{CC}$, Output Disabled	-5	+5	-5	+5	-5	+5	μA
I_{CC}	V_{CC} Operating Supply Current	$V_{CC} = \text{Max.}, I_{OUT} = 0 \text{ mA}, f = f_{MAX} = 1/t_{RC}$		240		220		200	mA
			L	210		190		175	
I_{SB1}	Automatic CE Power-Down Current — TTL Inputs	Max. V_{CC} , $\overline{CE} \geq V_{IH}$, $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$, $f = f_{MAX}$		40		40		40	mA
			L	20		20		20	
I_{SB2}	Automatic CE Power-Down Current — CMOS Inputs	Max. V_{CC} , $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$, or $V_{IN} \leq 0.3V$, $f=0$		10		10		10	mA
			L	1		1		1	

Shaded areas contain advance information.

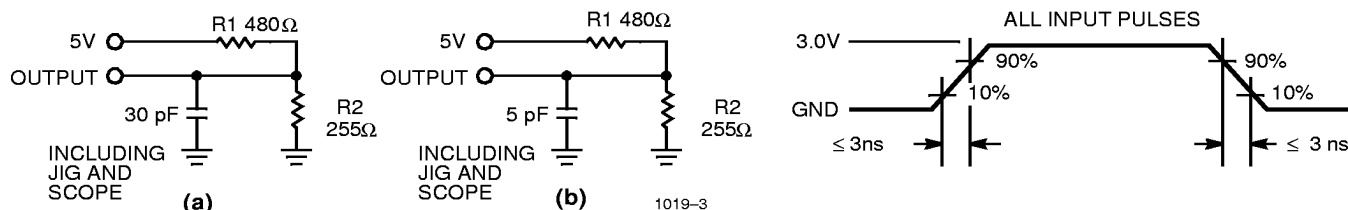
Capacitance^[3]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^\circ\text{C}, f = 1 \text{ MHz}, V_{CC} = 5.0V$	6	pF
C_{OUT}	Output Capacitance		8	pF

Notes:

- $V_{IL}(\text{min.}) = -2.0V$ for pulse durations of less than 20 ns.
- T_A is the "instant on" case temperature.
- Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



1019-4

Equivalent to: THÉVENIN EQUIVALENT
 OUTPUT — 167Ω — 1.73V

Switching Characteristics^[4] Over the Operating Range

Parameter	Description	7C1019-10		7C1019-12		7C1019-15		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE								
t _{RC}	Read Cycle Time	10		12		15		ns
t _{AA}	Address to Data Valid		10		12		15	ns
t _{OHA}	Data Hold from Address Change	3		3		3		ns
t _{ACE}	CE LOW to Data Valid		10		12		15	ns
t _{DOE}	OE LOW to Data Valid		5		6		7	ns
t _{LZOE}	OE LOW to Low Z	0		0		0		ns
t _{HZOE}	OE HIGH to High Z ^[5, 6]		5		6		7	ns
t _{LZCE}	CE LOW to Low Z ^[6]	3		3		3		ns
t _{HZCE}	CE HIGH to High Z ^[5, 6]		5		6		7	ns
t _{PU}	CE LOW to Power-Up	0		0		0		ns
t _{PD}	CE HIGH to Power-Down		10		12		15	ns
WRITE CYCLE ^[7,8]								
t _{WC}	Write Cycle Time	10		12		15		ns
t _{SCE}	CE LOW to Write End	8		9		10		ns
t _{AW}	Address Set-Up to Write End	7		8		10		ns
t _{HA}	Address Hold from Write End	0		0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		ns
t _{PWE}	WE Pulse Width	7		8		10		ns
t _{SD}	Data Set-Up to Write End	5		6		8		ns
t _{HD}	Data Hold from Write End	0		0		0		ns
t _{LZWE}	WE HIGH to Low Z ^[6]	3		3		3		ns
t _{HZWE}	WE LOW to High Z ^[5, 6]		5		6		7	ns

Shaded areas contain advance information.

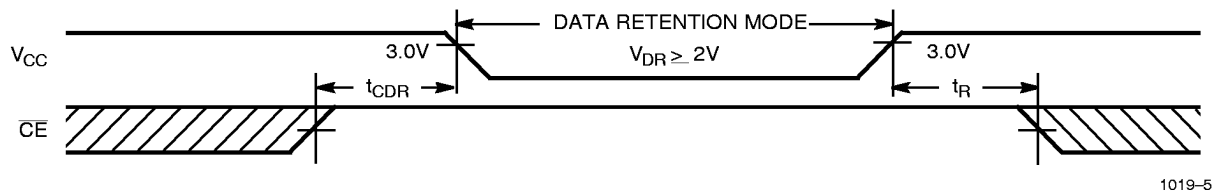
Note:

- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
- t_{HZOE} , t_{HZCE} , and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ± 500 mV from steady-state voltage.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
- The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. CE and WE must be LOW to initiate a write, and the transition of any of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- The minimum write cycle time for Write Cycle no. 3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD} .

Data Retention Characteristics Over the Operating Range (L Version Only)

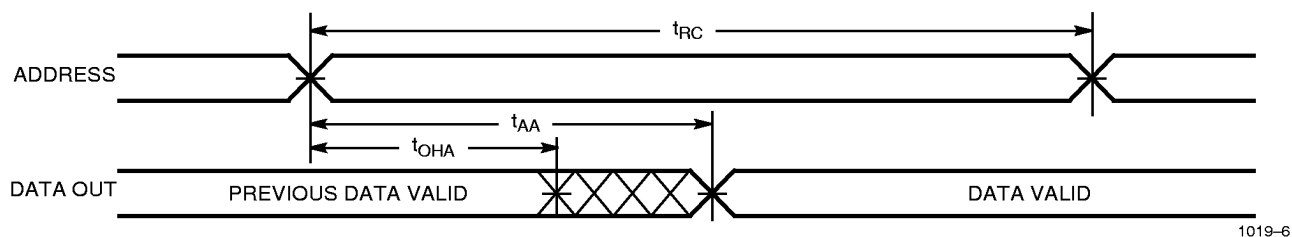
Parameter	Description	Conditions	Min.	Max	Unit
V_{DR}	V_{CC} for Data Retention	No input may exceed $V_{CC} + 0.5V$	2.0		V
I_{CCDR}	Data Retention Current	$V_{CC} = V_{DR} = 3.0V$, $\overline{CE}_1 \geq V_{CC} - 0.3V$		300	μA
$t_{CDR}^{[3]}$	Chip Deselect to Data Retention Time	$V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$	0		ns
t_R	Operation Recovery Time		t_{RC}		ns

Data Retention Waveform

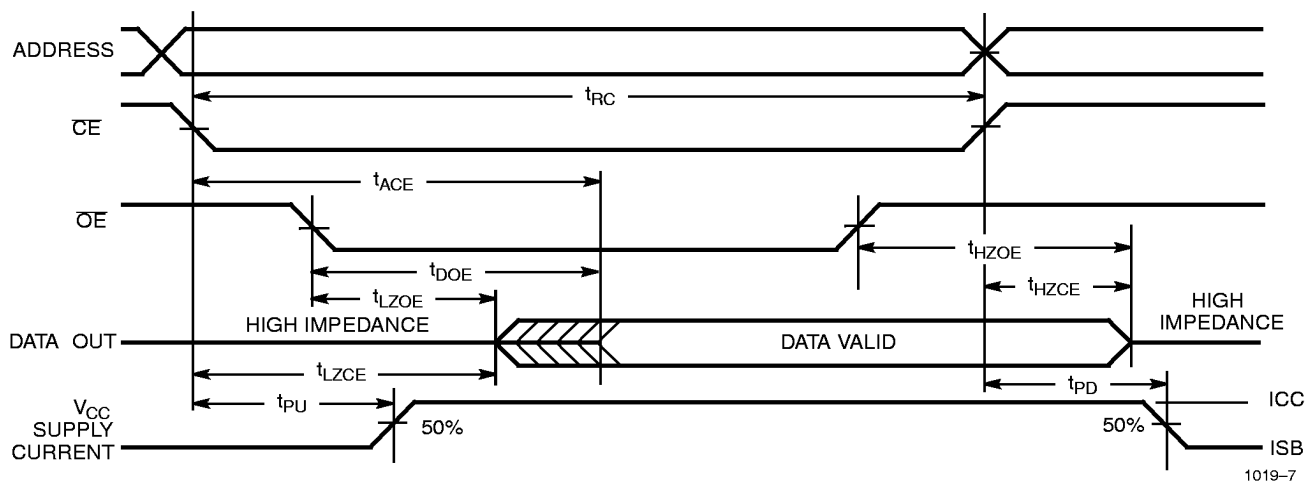


Switching Waveforms

Read Cycle No. 1^[9, 10]



Read Cycle No. 2 (OE Controlled)^[10, 11]

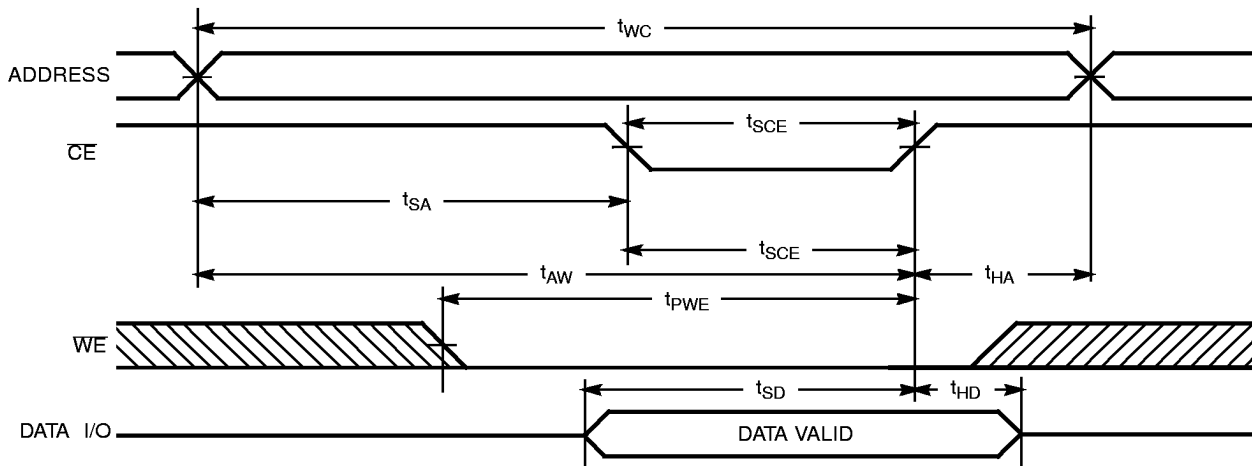


Notes:

9. Device is continuously selected. $\overline{OE}, \overline{CE} = V_{IL}$.
10. \overline{WE} is HIGH for read cycle.
11. Address valid prior to or coincident with \overline{CE} transition LOW.

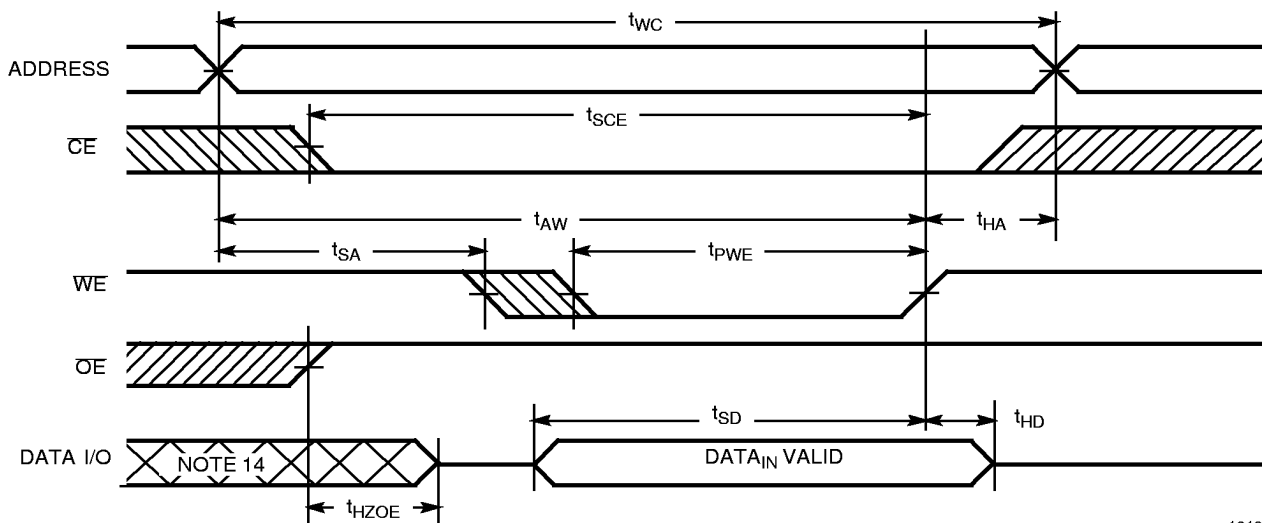
Switching Waveforms (continued)

Write Cycle No. 1 (CE Controlled)^[12, 13]



1019-8

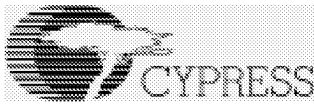
Write Cycle No. 2 (WE Controlled, OE HIGH During Write)^[12, 13]



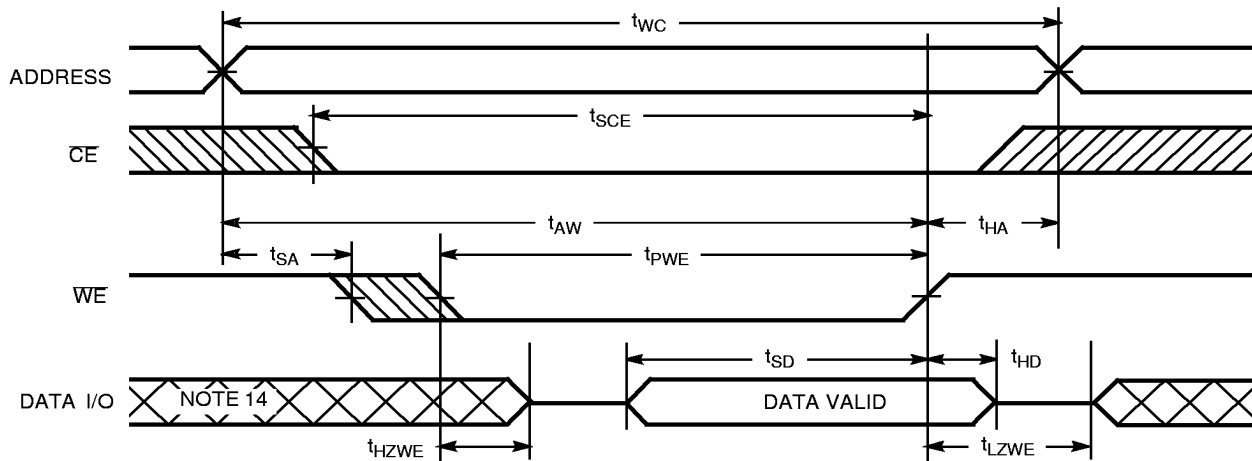
1019-9

Notes:

12. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
13. If \overline{CE} goes HIGH simultaneously with \overline{WE} going HIGH, the output remains in a high-impedance state.
14. During this period the I/Os are in the output state and input signals should not be applied.



Switching Waveforms (continued)

Write Cycle No. 3 (WE Controlled, OE LOW)^[13]

1019-10

Truth Table

CE	OE	WE	I/O ₀ -I/O ₇	Mode	Power
H	X	X	High Z	Power-Down	Standby (I _{SB})
X	X	X	High Z	Power-Down	Standby (I _{SB})
L	L	H	Data Out	Read	Active (I _{CC})
L	X	L	Data In	Write	Active (I _{CC})
L	H	H	High Z	Selected, Outputs Disabled	Active (I _{CC})

Document #: 38-00440-A

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
10	CY7C1019-10VC	V33	32-Lead 400-Mil Molded SOJ	Commercial
	CY7C1019L-10VC	V33	32-Lead 400-Mil Molded SOJ	
12	CY7C1019-12VC	V33	32-Lead 400-Mil Molded SOJ	Commercial
	CY7C1019L-12VC	V33	32-Lead 400-Mil Molded SOJ	
15	CY7C1019-15VC	V33	32-Lead 400-Mil Molded SOJ	Commercial
	CY7C1019L-15VC	V33	32-Lead 400-Mil Molded SOJ	

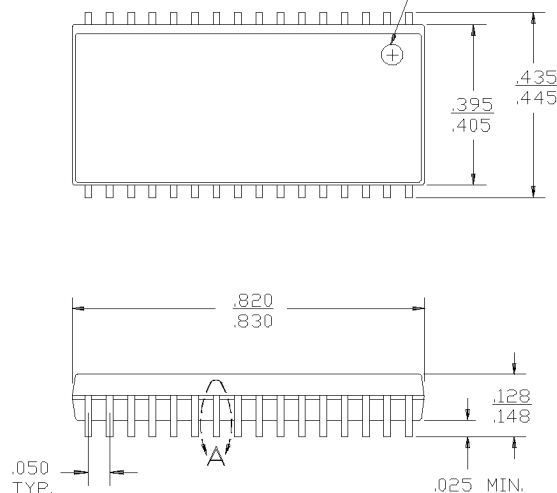
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Package Diagram

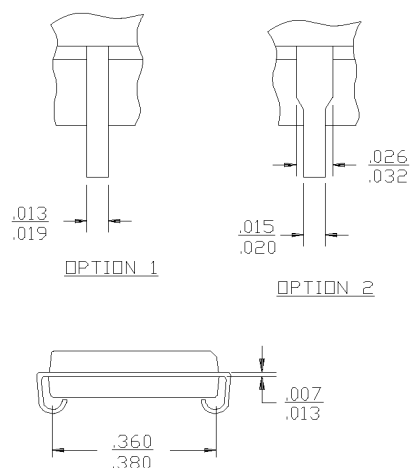
32-Lead (400-Mil) Molded SOJ V33

DIMENSIONS IN INCHES		MIN.	MAX.
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PIN 1 I.D



DETAIL A
EXTERNAL LEAD DESIGN



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